(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
29 May 2008 (29.05.2008)

PCT

(10) International Publication Number
WO 2008/063836 A1

(51) International Patent Classification:
H01L 21/3063 (2006.01)

(21) International Application Number:
PCT/US2007/083133

(22) International Filing Date: 31 October 2007 (31.10.2007)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
11/562,335 21 November 2006 (21.11.2006) US

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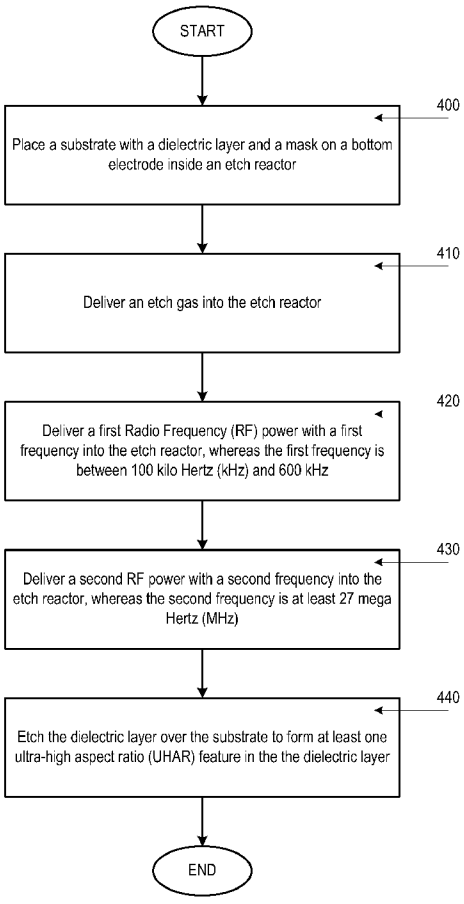
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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL, PL,

[Continued on next page]

(54) Title: REDUCING TWISTING IN ULTRA-HIGH ASPECT RATIO DIELECTRIC ETCH



(57) Abstract: An apparatus for etching a dielectric layer contained by a substrate is provided. An etch reactor comprises a top electrode and a bottom electrode. An etch gas source supplies an etch gas into the etch reactor. A first Radio Frequency (RF) source generates a first RF power with a first frequency and supplies the first RF power into the etch reactor, whereas the first frequency is between 100 kilo Hertz (kHz) and 600 kHz. A second RF source generates a second RF power with a second frequency and supplies the second RF power into the etch reactor, whereas the second frequency is at least 10 mega Hertz (MHz).

WO 2008/063836 A1

PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

— *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*